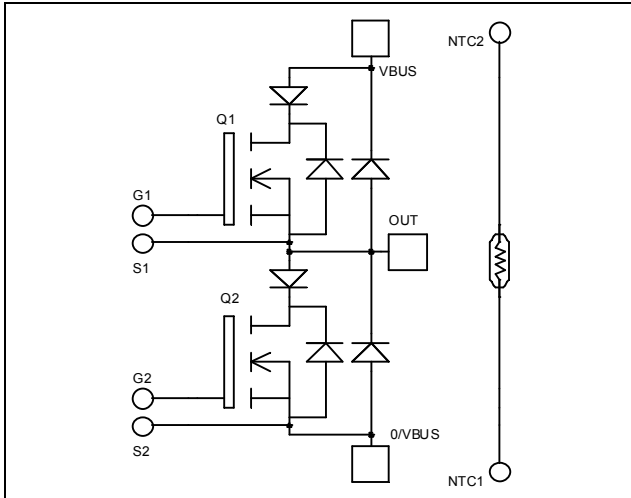


*Phase leg
Series & SiC parallel diodes
Super Junction
MOSFET Power Module*

**$V_{DSS} = 600V$
 $R_{DSon} = 35m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 72A \text{ @ } T_c = 25^\circ C$**

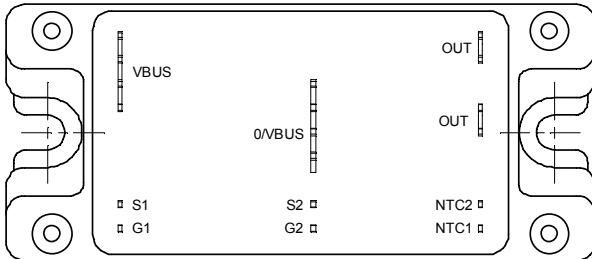


Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **COOLMOS**
Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
- **Parallel SiC Schottky Diode**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	72
		$T_c = 80^\circ C$	54
I_{DM}	Pulsed Drain current	288	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	35	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	416
I_{AR}	Avalanche current (repetitive and non repetitive)	20	A
E_{AR}	Repetitive Avalanche Energy	1	mJ
E_{AS}	Single Pulse Avalanche Energy	1800	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 500\mu A$	600			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V, T_j = 25^\circ\text{C}$			50	μA
		$V_{GS} = 0V, V_{DS} = 600V, T_j = 125^\circ\text{C}$			500	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 36A$			35	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2mA$	2.1	3	3.9	V
I_{GSS}	Gate - Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		14		nF
C_{oss}	Output Capacitance			5.13		
C_{rss}	Reverse Transfer Capacitance			0.42		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 300V$ $I_D = 72A$		518		nC
Q_{gs}	Gate - Source Charge			58		
Q_{gd}	Gate - Drain Charge			222		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 400V$ $I_D = 72A$ $R_G = 2.5\Omega$		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			283		
T_f	Fall Time			84		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		804		μJ
E_{off}	Turn-off Switching Energy ❶			1960		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		1315		μJ
E_{off}	Turn-off Switching Energy ❶			2412		

❶ In accordance with JEDEC standard JESD24-1.

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle, $T_c = 85^\circ\text{C}$		60		A
V_F	Diode Forward Voltage	$I_F = 60A$		1.1	1.15	V
		$I_F = 120A$		1.4		
		$I_F = 60A, T_j = 125^\circ\text{C}$		0.9		
t_{rr}	Reverse Recovery Time	$I_F = 60A, V_R = 133V, di/dt = 400A/\mu s, T_j = 25^\circ\text{C}$		24		ns
		$I_F = 60A, V_R = 133V, di/dt = 400A/\mu s, T_j = 125^\circ\text{C}$		48		
Q_{rr}	Reverse Recovery Charge	$I_F = 60A, V_R = 133V, di/dt = 400A/\mu s, T_j = 25^\circ\text{C}$		66		nC
		$I_F = 60A, V_R = 133V, di/dt = 400A/\mu s, T_j = 125^\circ\text{C}$		300		

Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I _{F(AV)}	Maximum Average Forward Current	50% duty cycle	T _c = 125°C		40		A
V _F	Diode Forward Voltage	I _F = 40A	T _j = 25°C		1.6	1.8	V
			T _j = 175°C		2.0	2.4	
Q _C	Total Capacitive Charge	I _F = 40A, V _R = 300V di/dt = 1200A/μs			56		nC
Q	Total Capacitance	f = 1MHz, V _R = 200V			260		pF
		f = 1MHz, V _R = 400V			200		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R _{thJC}	Junction to Case			0.3	°C/W
				0.65	
				0.8	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		100	
Torque	Mounting torque	To Heatsink	M5	4.7	N.m
Wt	Package Weight			160	g

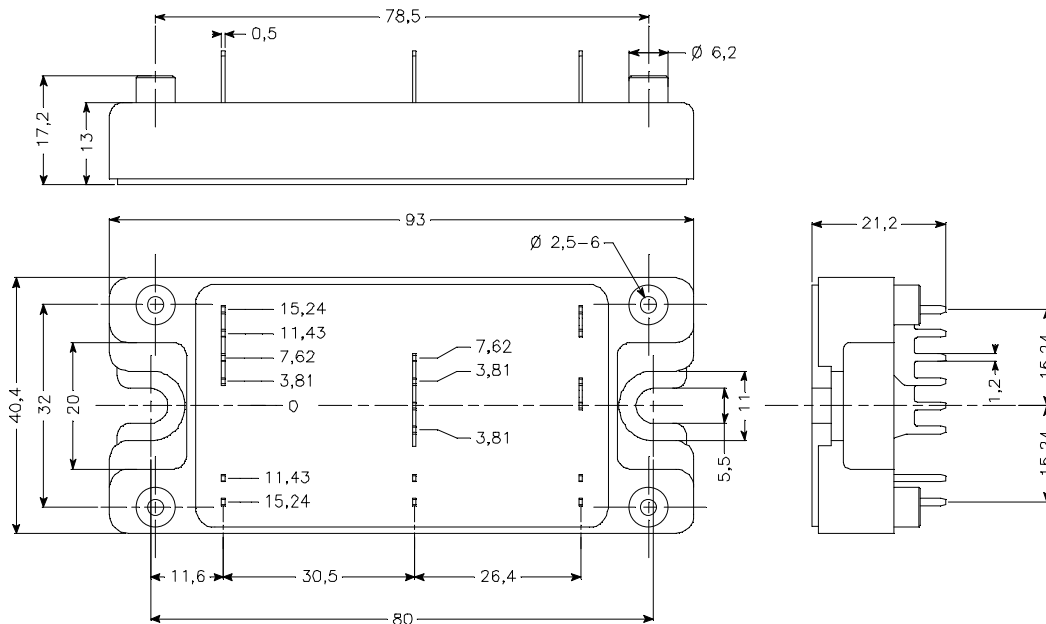
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		68		kΩ
B _{25/85}	T ₂₅ = 298.16 K		4080		K

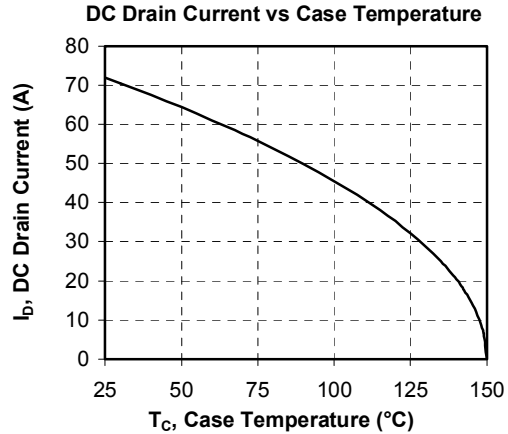
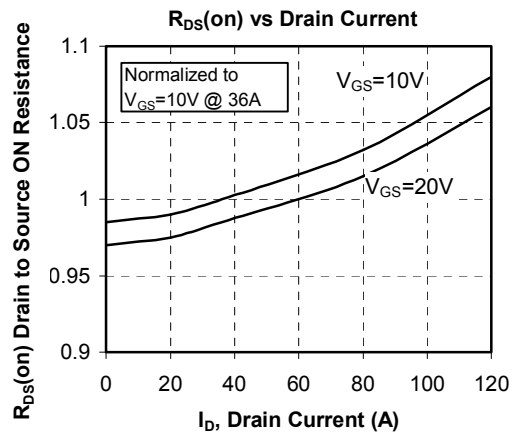
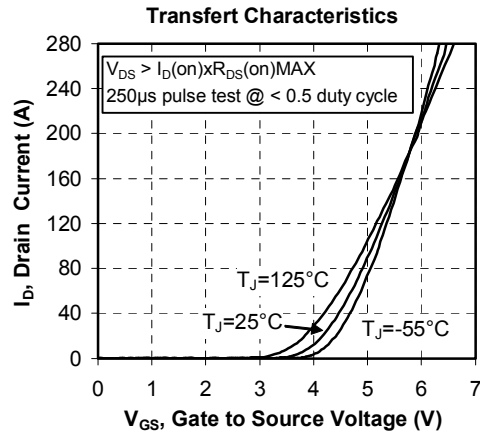
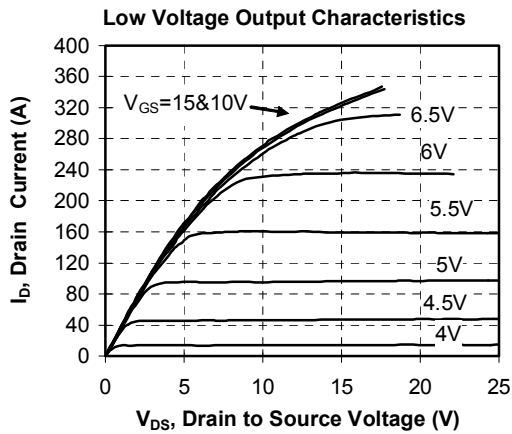
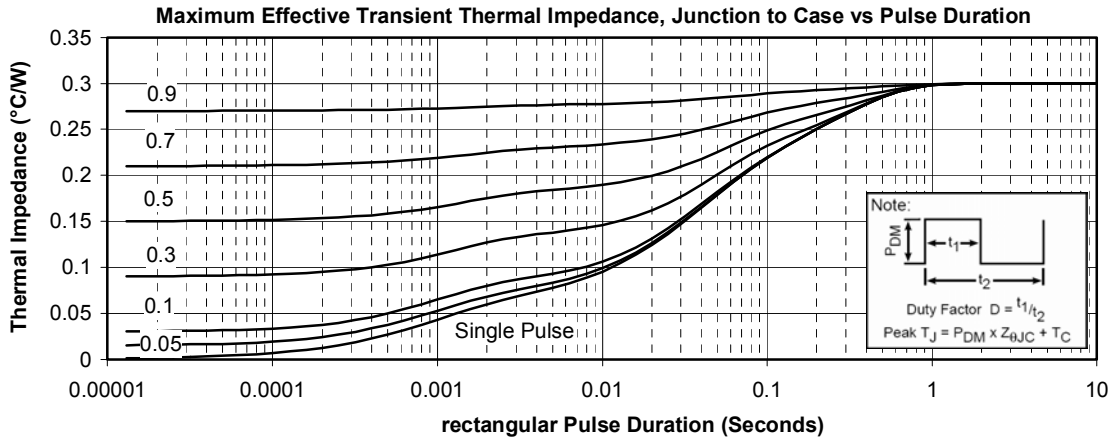
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

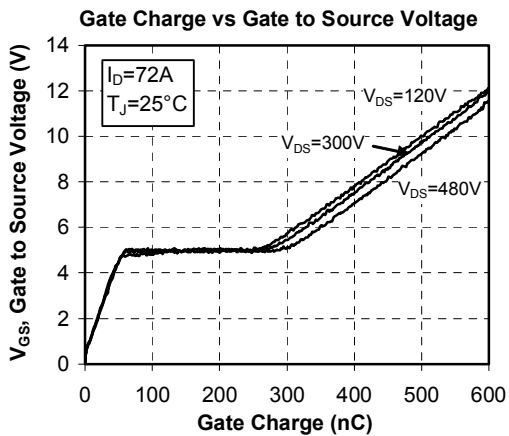
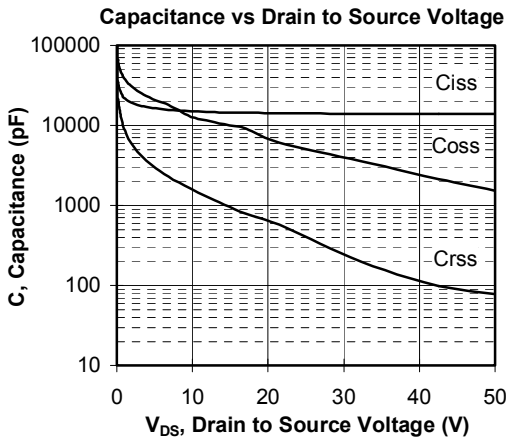
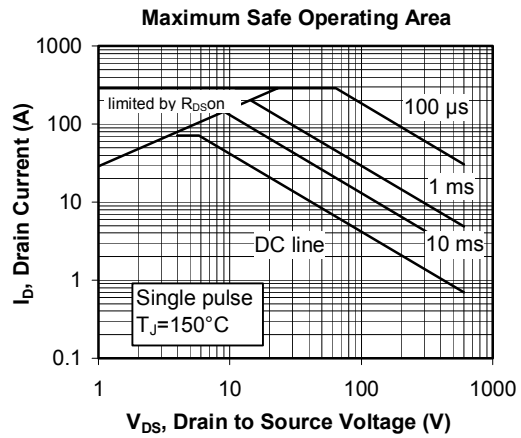
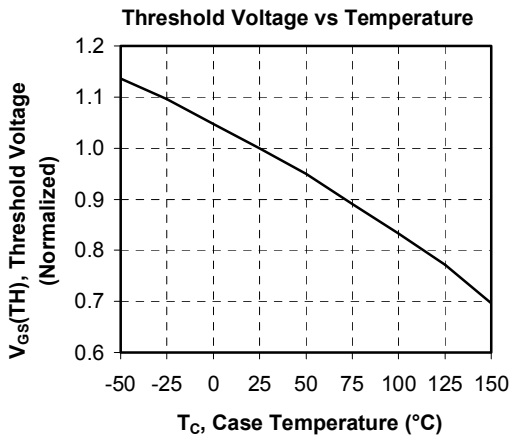
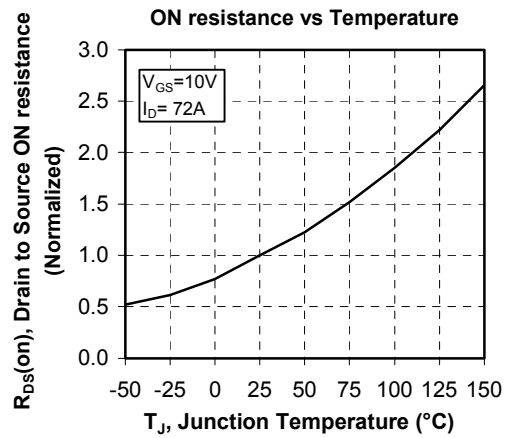
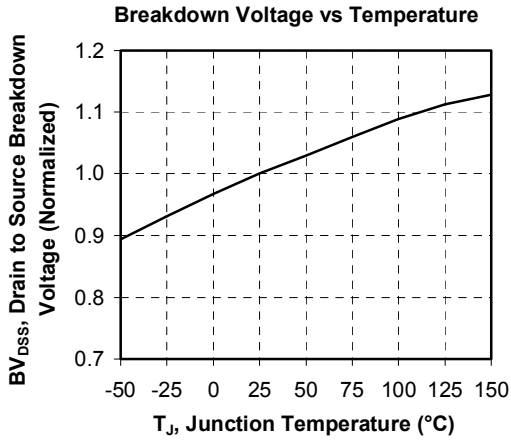
T: Thermistor temperature
R_T: Thermistor value at T

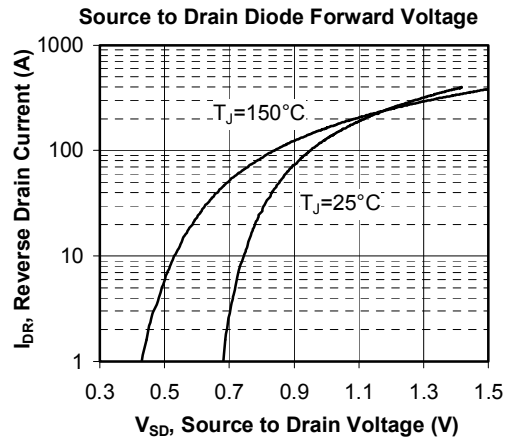
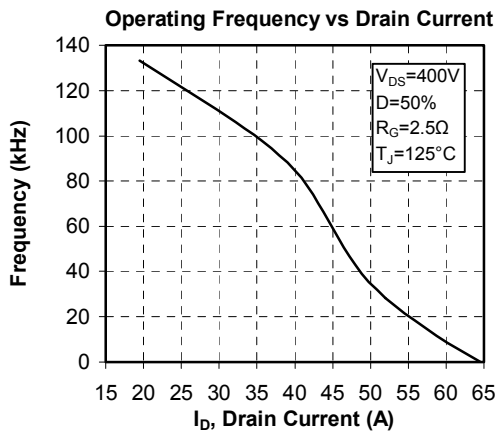
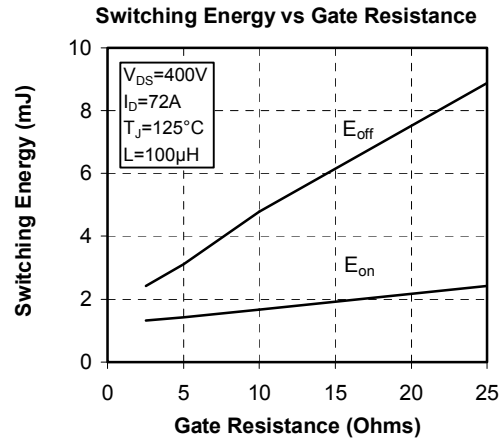
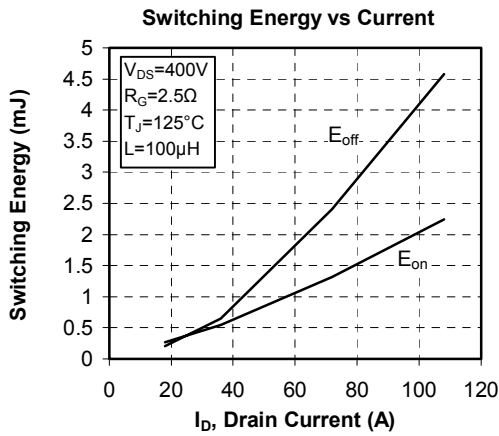
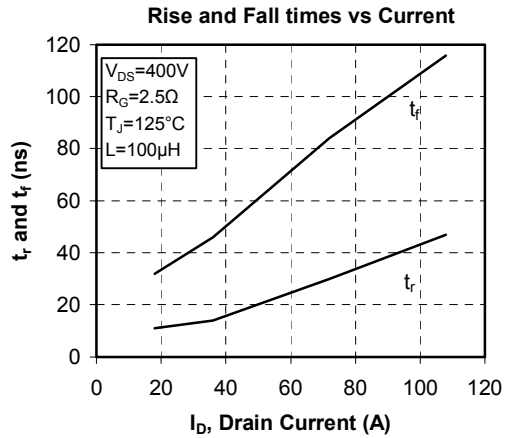
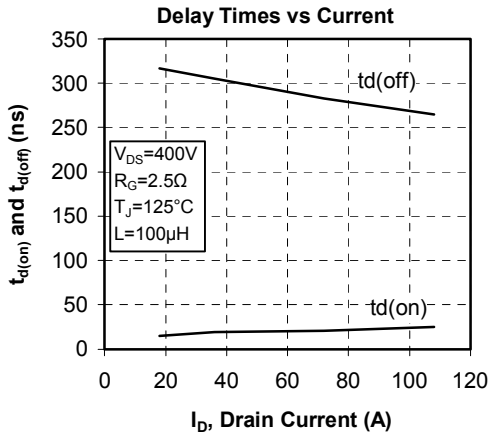
Package outline



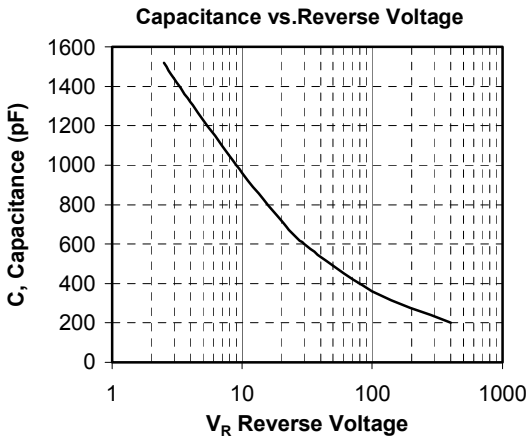
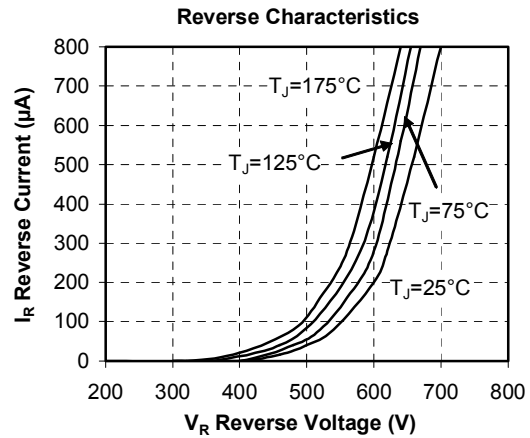
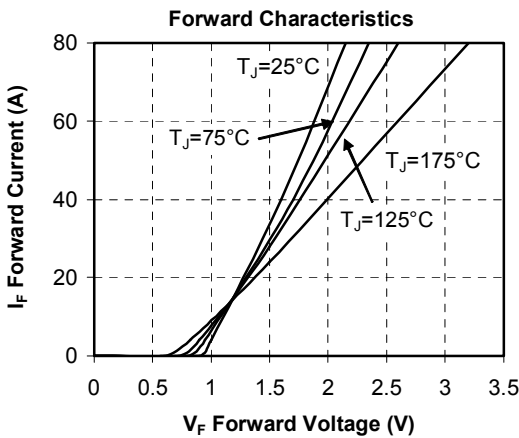
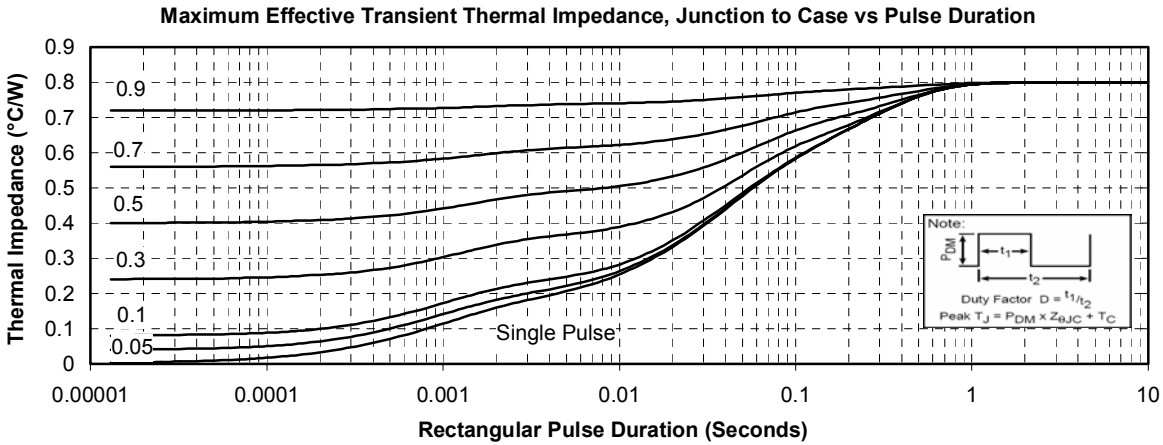
Typical CoolMOS Performance Curve







Typical SiC Diode Performance Curve



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APT's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.